

N-channel 30 V 13.6 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 3 — 24 October 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

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1.3 Applications

Quick reference data

Table 1.

- DC-to-DC converters
- Load switching

Synchronous buck regulator

1.4 Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	32	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	26	W
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; see <u>Figure 12</u>	-	14.4	16.9	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; see <u>Figure 12</u>	-	11.6	13.6	mΩ
Dynamic ch	naracteristics					
Q _{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	1.2	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 15 V; see Figure 14; see Figure 15	-	4	-	nC

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		5
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	$\begin{array}{c} \hline \\ \hline \\ 1 \\ 2 \\ 3 \\ 4 \\ \end{array}$	mbb076 S

SOT669 (LFPAK; Power-SO8)

3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN013-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669			

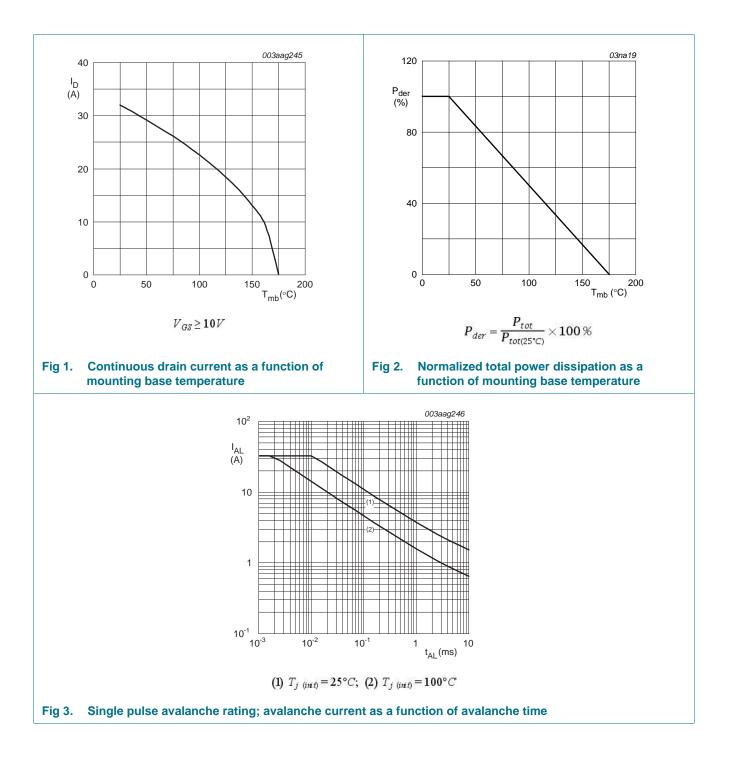
4. Limiting values

Table 4.Limiting values

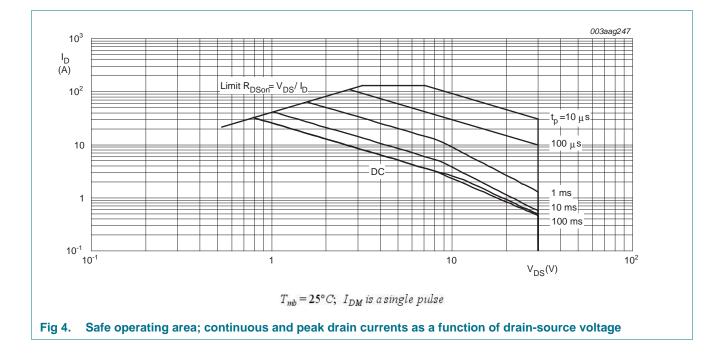
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 kΩ	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	32	А
		V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	23	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 4</u>	-	130	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	26	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	130	-	V
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	23	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu$ s; $T_{mb} = 25 \ ^{\circ}C$	-	130	А
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 ^{\circ}\text{C}; \text{I}_\text{D} = 32 \text{ A}; \\ V_{sup} \leq 30 \text{ V}; \text{R}_{GS} = 50 \Omega; \text{ unclamped}; \\ \text{see } \underline{\text{Figure } 3} \end{array} $	-	7	mJ

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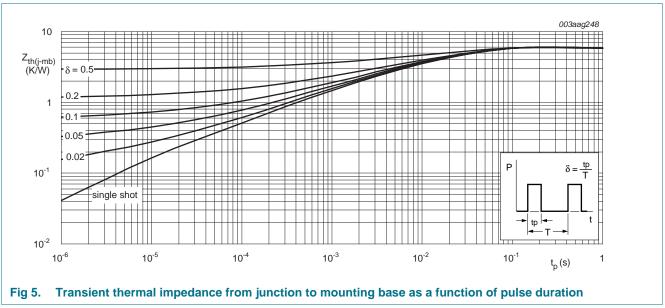
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 5	-	5.66	5.83	K/W



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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	30	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.68	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; see <u>Figure 12</u>	-	14.4	16.9	mΩ
		V_{GS} = 4.5 V; I_D = 10 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	27.2	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; see <u>Figure 12</u>	-	11.6	13.6	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	22.1	mΩ
R _G	gate resistance	f = 1 MHz	-	2.12	4.24	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	8.3	-	nC
		$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	7.7	-	nC
Q _{GS}	gate-source charge	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	1.3	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	0.9	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.4	-	nC
Q _{GD}	gate-drain charge		-	1.2	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	2.7	-	V
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$	-	521	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	128	-	pF
C _{rss}	reverse transfer capacitance		-	39	-	pF
d(on)	turn-on delay time	V_{DS} = 15 V; R_{L} = 0.6 Ω; V_{GS} = 4.5 V;	-	11.6	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	9.9	-	ns
d(off)	turn-off delay time		-	16.3	-	ns
t _f	fall time		-	6.2	-	ns

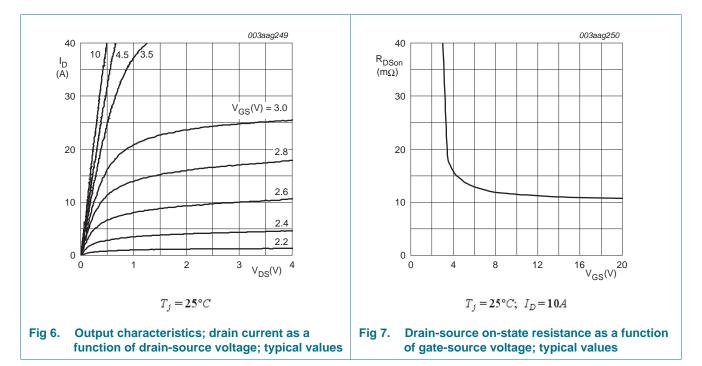
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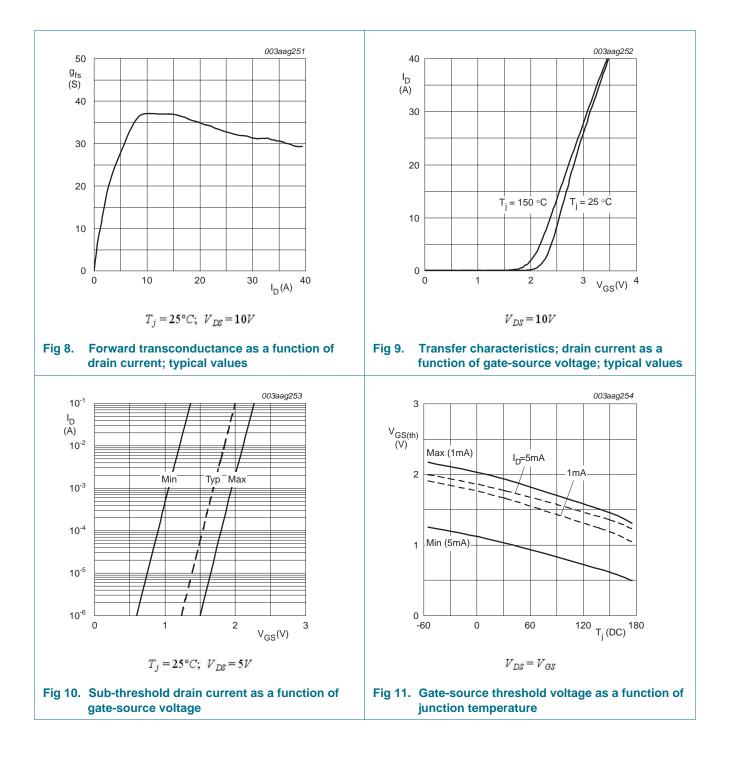
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Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	V_{GS} = 0 V; V_{DS} = 15 V; f = 1 MHz; T _j = 25 °C	-	3.3	-	nC
Source-dra	in diode					
V _{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 17	-	0.86	1.1	V
t _{rr}	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	16	-	ns
Q _r	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	6	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 V; I_S = 10 A;$	-	9.5	-	ns
t _b	reverse recovery fall time	$dI_S/dt = -100 A/\mu s; V_{DS} = 15 V;$ see Figure 18	-	6.5	-	ns

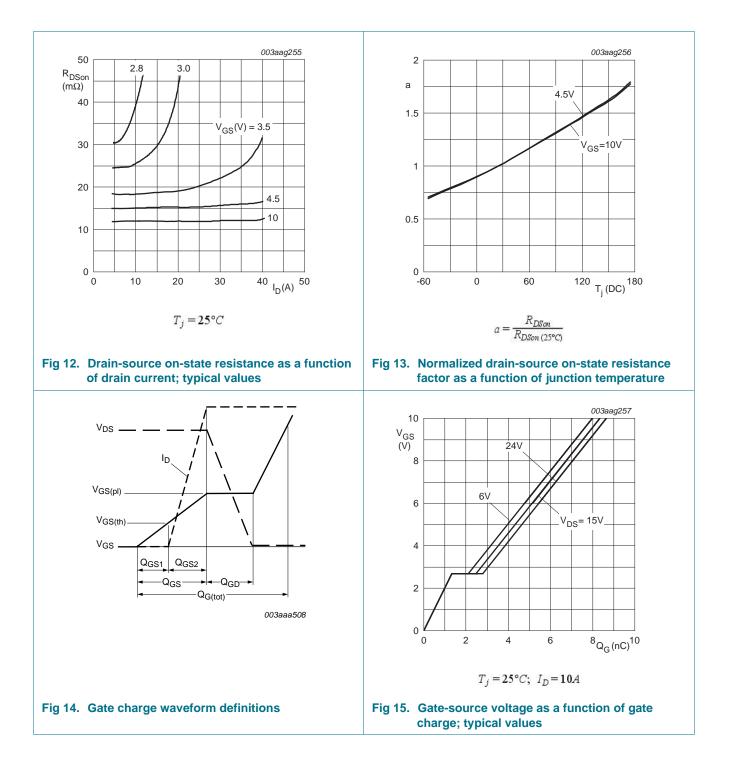


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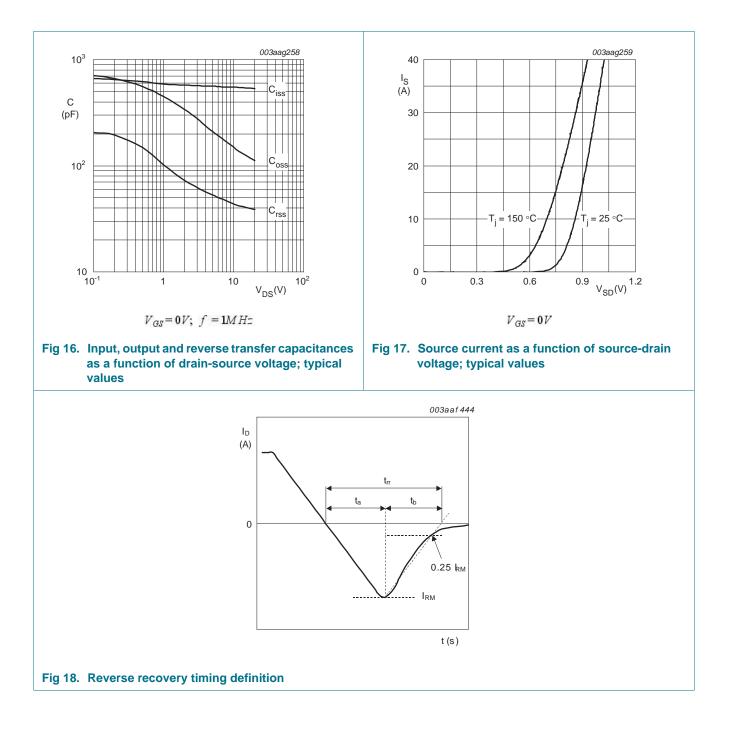


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7. Package outline

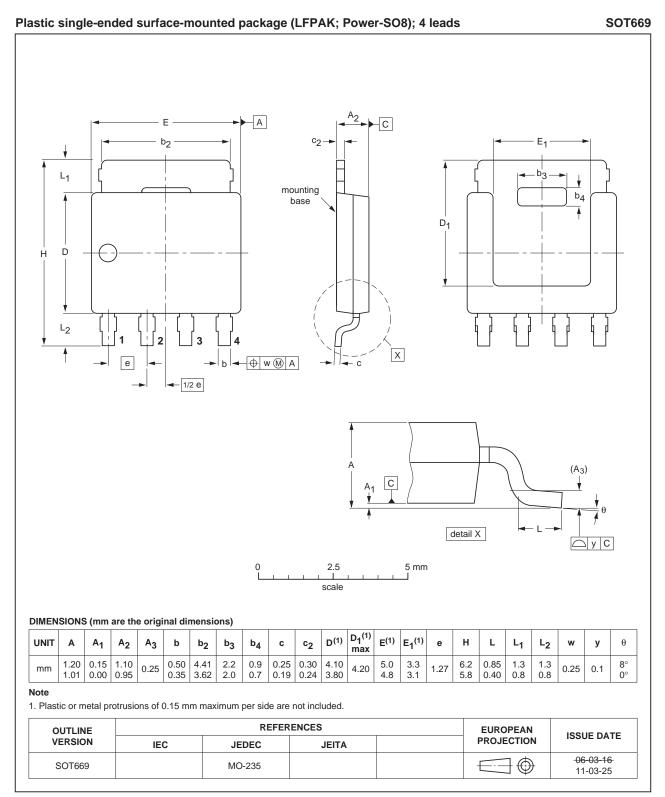


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN013-30YLC v.3	20111024	Product data sheet	-	PSMN013-30YLC v.2
Modifications:	 Status change 	ed from preliminary to produc	ot.	
	 Various change 	jes to content.		
PSMN013-30YLC v.2	20110929	Preliminary data shee	·t -	PSMN013-30YLC v.1

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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